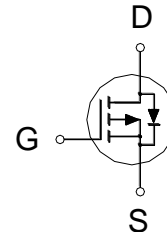




PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
-30V	14mΩ	-8A

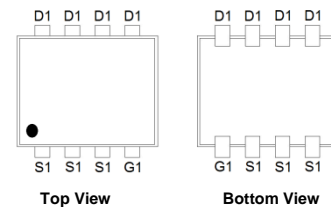


Features

- Pb-Free, Halogen Free and RoHS compliant.
- Low $R_{DS(on)}$ to Minimize Conduction Losses.
- Ohmic Region Good $R_{DS(on)}$ Ratio.
- Optimized Gate Charge to Minimize Switching Losses.

Applications

- Protection Circuits Applications.
- Logic/Load Switch Circuits Applications.



G : GATE
D : DRAIN
S : SOURCE

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ °C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	±25	V
Continuous Drain Current	$T_A = 25\text{ °C}$	I_D	-8	A
	$T_A = 70\text{ °C}$		-6.4	
Pulsed Drain Current ¹		I_{DM}	-50	
Avalanche Current		I_{AS}	-25.7	
Avalanche Energy	L = 0.1mH	E_{AS}	33	mJ
Power Dissipation	$T_A = 25\text{ °C}$	P_D	1.6	W
	$T_A = 70\text{ °C}$		1	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient	$R_{\theta JA}$		76	°C / W

¹Pulse width limited by maximum junction temperature.

ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

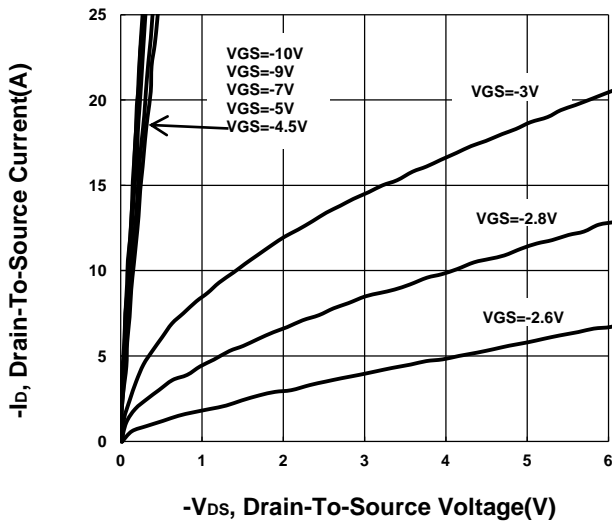
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-1.1	-1.7	-2.1	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±25V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -24V, V _{GS} = 0V			-1	μA
		V _{DS} = -20V, V _{GS} = 0V, T _J = 70 °C			-10	
Drain-Source On-State Resistance ¹	R _{DS(ON)}	V _{GS} = -4.5V, I _D = -8A		17	22	mΩ
		V _{GS} = -10V, I _D = -8A		11.3	14	
Forward Transconductance ¹	g _{fs}	V _{DS} = -5V, I _D = -8A		33		S
DYNAMIC						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = -15V, f = 1MHz		1634		pF
Output Capacitance	C _{oss}			250		
Reverse Transfer Capacitance	C _{rss}			189		
Gate Resistance	R _g	V _{GS} = 0V, V _{DS} = 0V, f = 1MHz		4.2		Ω
Total Gate Charge ²	Q _g	V _{DS} = -15V, V _{GS} = -10V, I _D = -8A		32		nC
Gate-Source Charge ²	Q _{gs}			4.1		
Gate-Drain Charge ²	Q _{gd}			7.5		
Turn-On Delay Time ²	t _{d(on)}	V _{DS} = -15V, I _D ≅ -8A, V _{GS} = -10V, R _G = 6 Ω		16		nS
Rise Time ²	t _r			54		
Turn-Off Delay Time ²	t _{d(off)}			64		
Fall Time ²	t _f			90		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS						
Continuous Current	I _S				-1.3	A
Forward Voltage ¹	V _{SD}	I _F = -8A, V _{GS} = 0V			-1.2	V
Reverse Recovery Time	t _{rr}	I _F = -8A, dI _F /dt = 100A / μS		19		nS
Reverse Recovery Charge	Q _{rr}				8	

¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

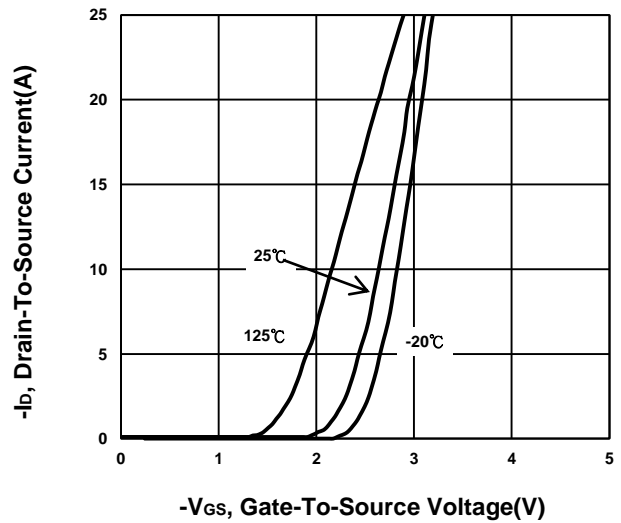
²Independent of operating temperature.

³Pulse width limited by maximum junction temperature.

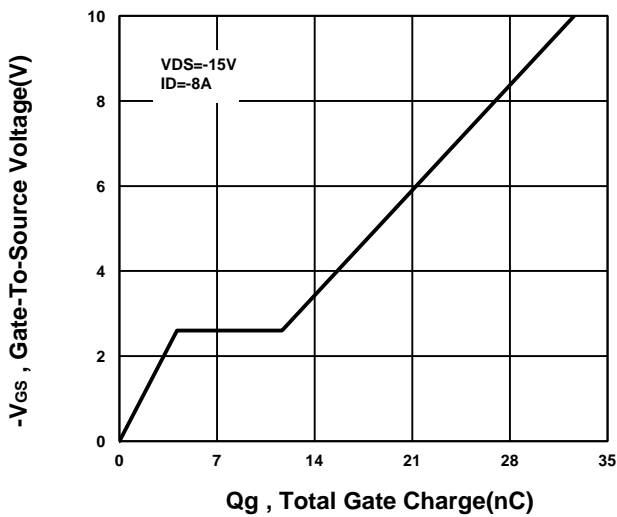
Output Characteristics



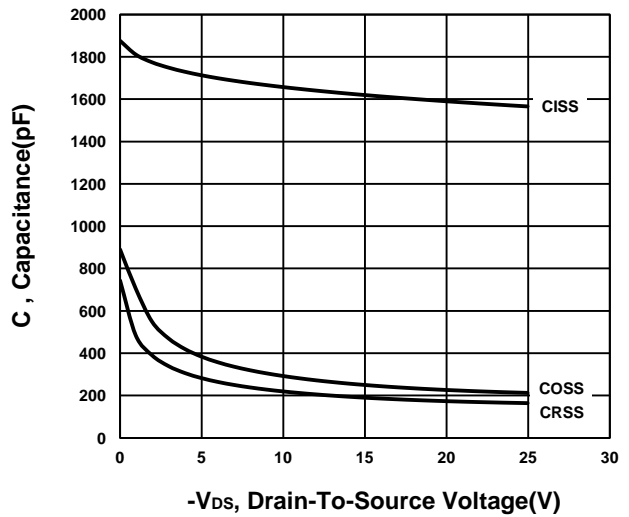
Transfer Characteristics



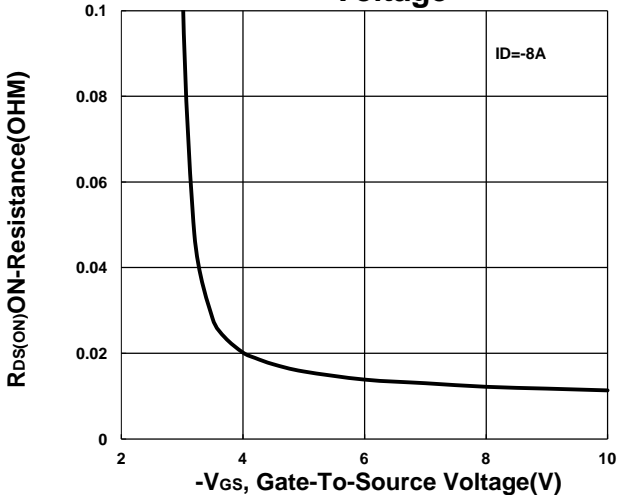
Gate charge Characteristics



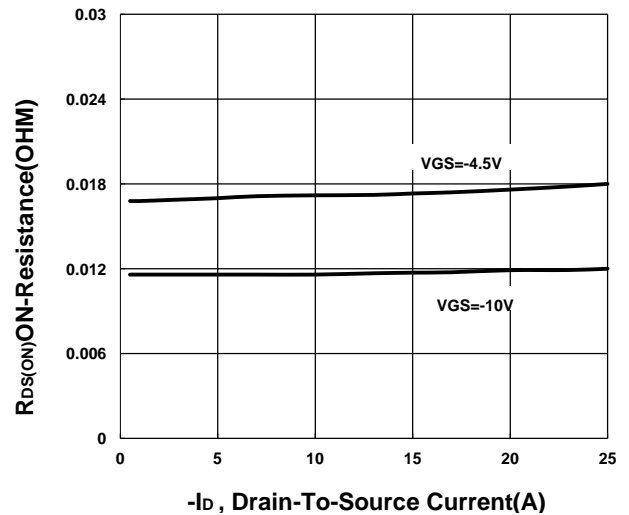
Capacitance Characteristic



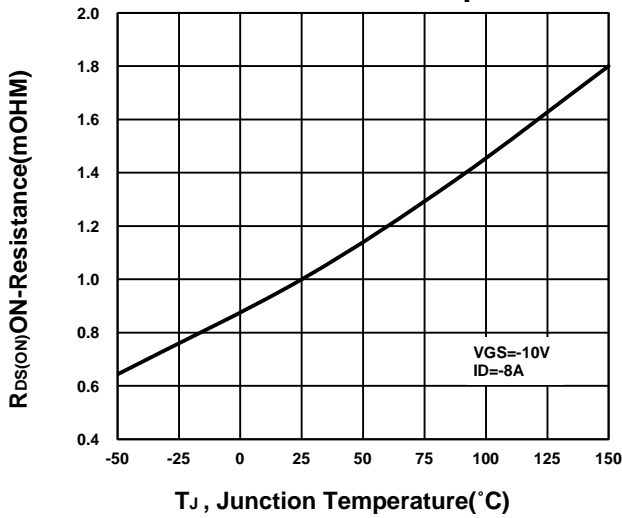
On-Resistance VS Gate-To-Source Voltage



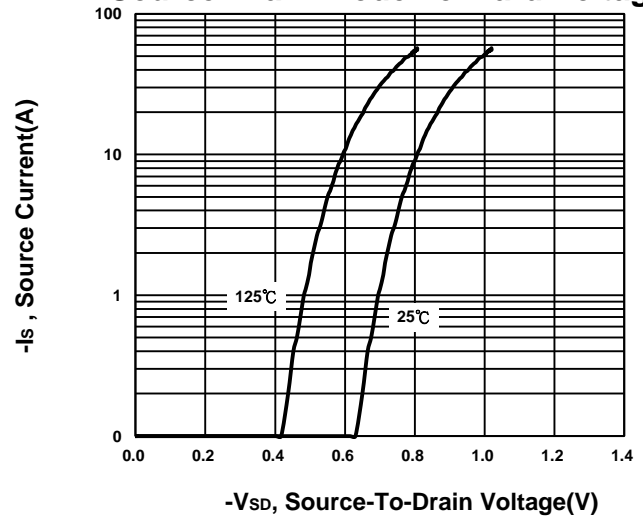
On-Resistance VS Drain Current



On-Resistance VS Temperature

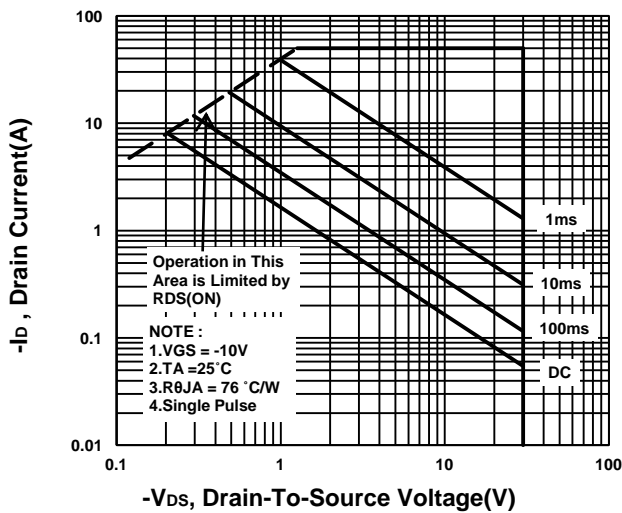


Source-Drain Diode Forward Voltage

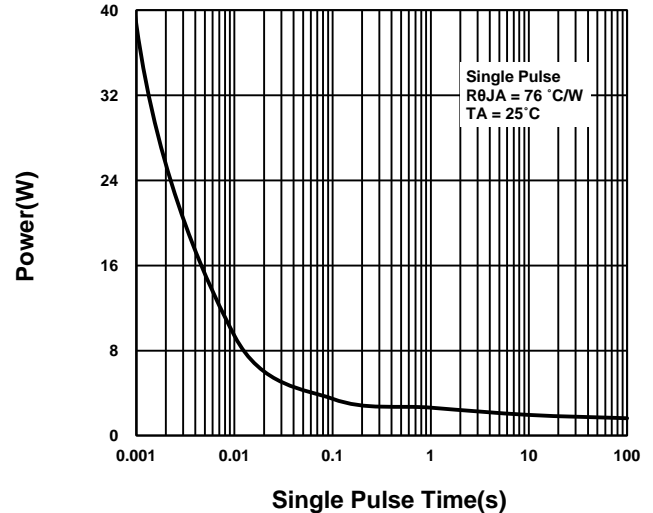


T_J, Junction Temperature(°C)

Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve

